Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series BT" triac will commutate the full RMS current at the maximum rated junction temperature ($T_{j(max)}$ = 150 °C) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

2. Features and benefits

- · 3Q technology for improved noise immunity
- · High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High junction operating temperature capability
- · High voltage capability
- · Least sensitive gate for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- · Applications subject to high temperature
- Heating controls
- · High power motor control
- · High power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit
Absolute	maximum rating			
V_{DRM}	repetitive peak off-state voltage		800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 122 °C; Fig. 1; Fig. 2; Fig. 3	20	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; t_p = 20 ms; $T_{j(init)}$ = 25 °C; Fig. 4; Fig. 5	200	А
		full sine wave; t_p = 16.7 ms; $T_{j(init)}$ = 25 °C	220	Α
T _j	junction temperature		150	°C

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-} $ $T_j = 25 \text{ °C; } Fig. 7$	-	-	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	40	mA
V _T	on-state voltage	I _T = 24 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
Dynamic	characteristics					'
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 150 °C; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; gate open circuit	1800	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 150 \text{ °C}; I_{T(RMS)} = 20 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s}; gate open circuit};$	25	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 150 ^{\circ}\text{C}; I_{T(RMS)} = 20 \text{ A};$ $dV_{com}/dt = 1 \text{ V}/\mu\text{s}; gate open circuit}$	65	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2	}	sym051
3	G	gate		Symoor
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package	Orderable part number	•	Small packing	Package	Package
	name		method	quantity	version	issue date
BTA420-800BT	TO-220	BTA420-800BT	Tube	50	SOT78	8-Jun-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes
BTA420-800BT	BTA420-800BT

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 122^{\circ}C$; Fig. 1; Fig. 2; Fig. 3	20	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; t_p = 20 ms; $T_{j(init)}$ = 25 °C; Fig. 4; Fig. 5	200	А
		full sine wave; t_p = 16.7 ms; $T_{j(init)}$ = 25 °C	220	А
l ² t	I ² t for fusing	t _p = 10ms; sine wave	200	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 100 mA	100	A/µs
I _{GM}	peak gate current		2	А
P _{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C

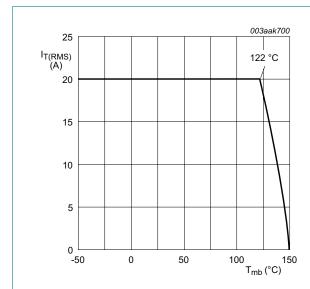


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

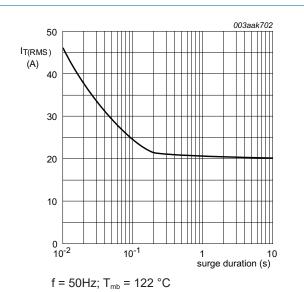


Fig. 2. RMS on-state current as a function of surge duration; maximum values

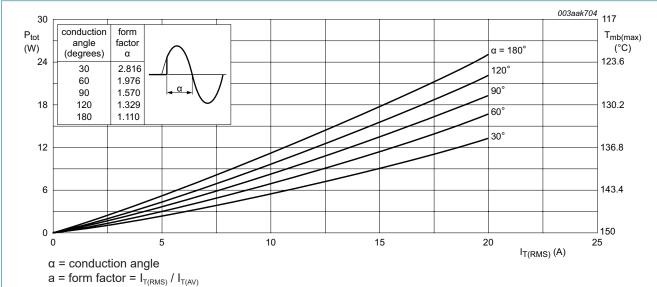


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

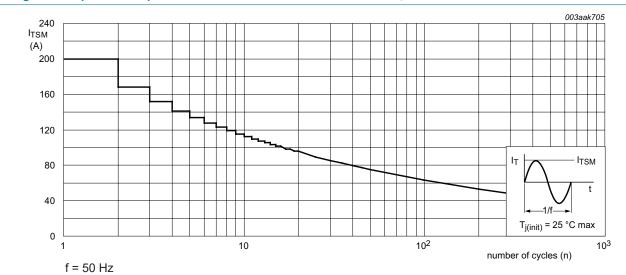
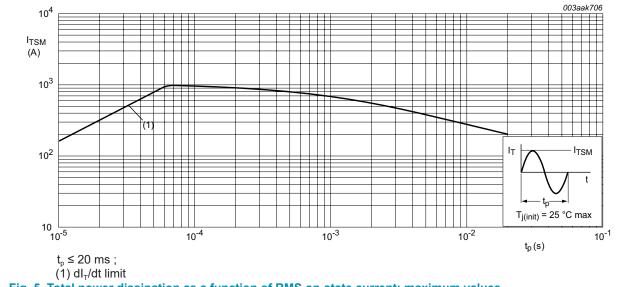


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



9. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance	full cycle; Fig. 6	-	-	1.1	K/W
	from junction to mounting base	half cycle; <u>Fig. 6</u>	-	-	1.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

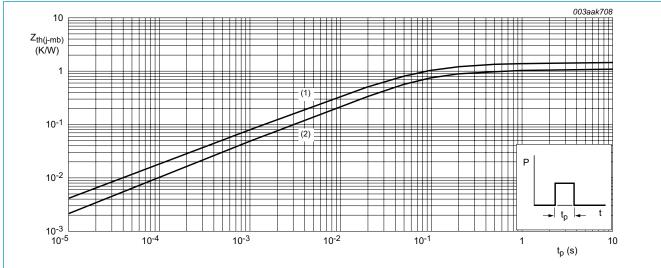
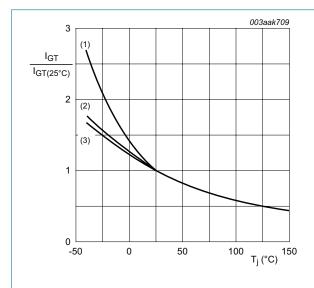


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	50	mA
IL	latching current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	60	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	90	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 8}}$	-	-	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	60	mA
V _T	on-state voltage	I _τ = 10 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 \text{ °C};$ Fig. 11	0.2	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 25 °C	-	0.2	1	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_{j} = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	1800	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V; } T_j = 150 ^{\circ}\text{C; } I_{T(RMS)} = 20 \text{ A; } dV_{com}/dt = 10 \text{ V/}\mu\text{s; gate open circuit; } snubberless condition}$	25	-	-	A/ms
		$V_D = 400 \text{ V; } T_j = 150 \text{ °C; } I_{T(RMS)} = 20 \text{ A;}$ $dV_{com}/dt = 1 \text{ V/}\mu\text{s; gate open circuit}$	65	-	-	A/ms



(1) T2- G-

(2) T2+ G-

(3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

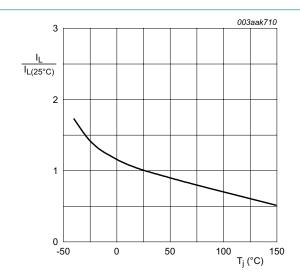


Fig. 8. Normalized latching current as a function of junction temperature

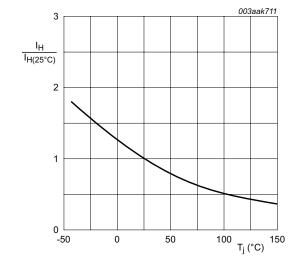
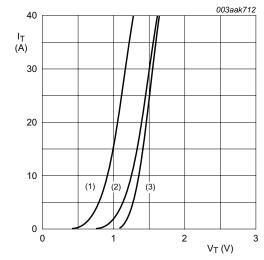


Fig. 9. Normalized holding current as a function of junction temperature



 $V_o = 1.087 \text{ V}; R_s = 0.014 \Omega$

(1) T_i = 150 °C; typical values

(2) T_j = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

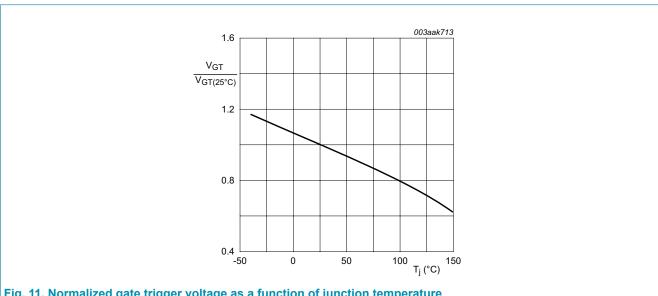
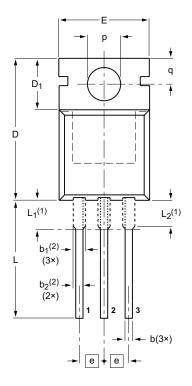


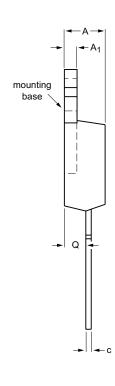
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

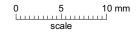
11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78







DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ ⁽²⁾	b ₂ (2)	U	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 11 March 2020

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